





ZXMN3A14F

#### 30V N-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

BV <sub>DSS</sub>	Max R <sub>DS(on)</sub>	Max I <sub>D</sub> T <sub>A</sub> = 25°C  (Note 4)		
30V	65m $Ω$ @ V <sub>GS</sub> = 10V	3.2A		
30 V	95mΩ @ $V_{GS} = 4.5V$	2.6A		

### **Description and Applications**

This MOSFET utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed, making it ideal for high-efficiency power management applications.

- DC DC converters
- Power management functions
- Disconnect switches
- Motor control

#### **Features and Benefits**

- Low on-resistance
- Fast switching speed
- Low gate charge
- Low threshold
- Totally Lead-Free & Fully RoHS compliant (Note 1)
- Halogen and Antimony Free. "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

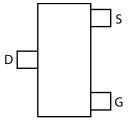
#### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Copper leadframe Solderable per MIL-STD-202, Method 208
- Weight: 0.008 grams (approximate)

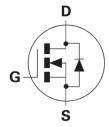




Top View



Top View Pin Out



**Equivalent Circuit** 

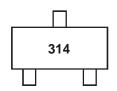
### **Ordering Information (Note 3)**

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN3A14FTA	314	7	8	3000 Units

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 3. For more packaging details, go to our website at http://www.diodes.com.

# Marking Information



314 = Product Type Marking Code





# **Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic				Symbol	Value	Units
Drain-Source Voltage				$V_{DSS}$	30	V
Gate-Source Voltage				$V_{GS}$	±20	V
Continuous Drain Current	V <sub>GS</sub> = 10V	T <sub>A</sub> = 70°C	(Note 5) (Note 5) (Note 4)	$I_{D}$	3.9 3.2 3.2	А
Pulsed Drain Current (Note 6)				$I_{DM}$	18	A
Continuous Source Current (Body Diode) (Note 5)				Is	2.3	A
Pulsed Source Current (Body Diode) (Note 6)				I <sub>SM</sub>	18	A

## Thermal Characteristics @TA = 25°C unless otherwise specified

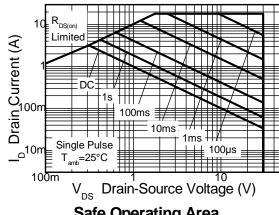
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4)	D-	1	W
Linear Derating Factor	P <sub>D</sub>	8	mW/°C
Power Dissipation (Note 5)	D-	1.5	W
Linear Derating Factor	P <sub>D</sub>	12	mW/°C
Thermal Resistance, Junction to Ambient (Note 4)	R <sub>0</sub> JA	125	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	83	°C/W
Thermal Resistance, Junction to Leads (Note 7)	$R_{ heta JL}$	70.44	°C/W
Operating and Storage Temperature Range	$T_{J_i} T_{STG}$	-55 to +150	°C

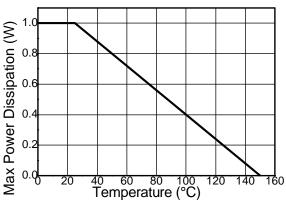
Notes:

- 4. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions 5. For a device surface mounted on FR4 PCB measured at t ≤5 secs.
  6. Repetitive rating 25mm x 25mm FR4 PCB, D=0.02 pulse width=300µs pulse current limited by maximum junction temperature.
  7. Thermal resistance from junction to solder-point (at the end of the drain lead).



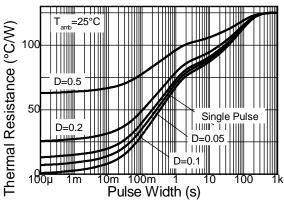
## **Thermal Characteristics**

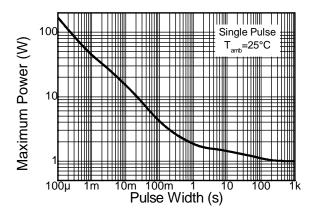




**Safe Operating Area** 







**Transient Thermal Impedance** 

**Pulse Power Dissipation** 





**Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

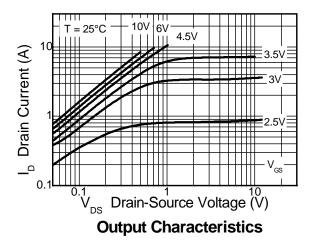
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage		30			V	$I_D = 250 \mu A, V_{GS} = 0 V$
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μΑ	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$
ON CHARACTERISTICS						
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.0		2.2	V	$I_D = 250 \mu A, V_{DS} = V_{GS}$
Static Drain-Source On-Resistance (Note 8)	D		48	65	mΩ	$V_{GS} = 10V, I_D = 3.2A$
Static Dialif-Source Off-Resistance (Note o)	R <sub>DS</sub> (ON)		69	95		$V_{GS} = 4.5V, I_D = 2.6A$
Forward Transconductance (Notes 8 and 10)	g <sub>fs</sub>	_	7.1		S	$V_{DS} = 15V, I_D = 3.2A$
Diode Forward Voltage (Note 8)	$V_{SD}$	_	0.85	0.95	V	$T_J = 25$ °C, $I_S = 2.5$ A, $V_{GS} = 0$ V
Reverse Recovery Time (Note 10)	t <sub>rr</sub>	_	13		ns	$T_J = 25$ °C, $I_F = 1.6$ A,
Reverse Recovery Charge (Note 10)	Qrr	_	7	_	nC	di/dt = 100A/μs
DYNAMIC CHARACTERISTICS (Note 10)	•				•	
Input Capacitance	C <sub>iss</sub>	_	448			15// 1/
Output Capacitance	Coss	_	82		pF	$V_{DS} = 15V$ , $V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	C <sub>rss</sub>	_	49			
Turn-On Delay Time (Note 9)	t <sub>D(on)</sub>	_	2.4			
Turn-On Rise Time (Note 9)	t <sub>r</sub>	_	2.5		no	$V_{DD} = 15V, I_D = 1A,$
Turn-Off Delay Time (Note 9)	t <sub>D(off)</sub>	_	13.1	_	ns	$R_G \cong 6.0\Omega, \ V_{GS} = 10V$
Turn-Off Fall Time (Note 9)	t <sub>f</sub>	_	5.3	_		
Total Gate Charge (Note 9)	Qg	_	8.6	_	1, 451, 1, 451,	
Gate-Source Charge (Note 9)	Qgs	_	1.4	_	nC	$V_{DS} = 15V$ , $V_{GS} = 10V$ , $I_{D} = 3.2A$
Gate-Drain Charge (Note 9)	$Q_{gd}$	_	1.8	_		ID = 3.2A

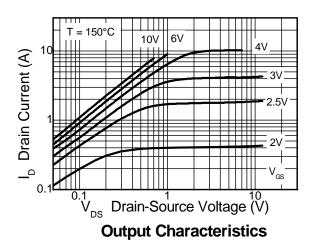
Notes:

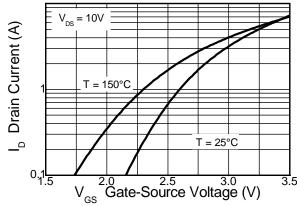
<sup>8.</sup> Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤ 2%.
9. Switching characteristics are independent of operating junction temperature.
10. For design aid only, not subject to production testing.

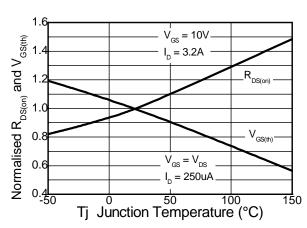


# **Typical Characteristics**



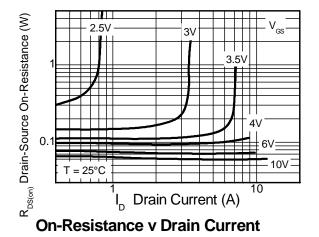


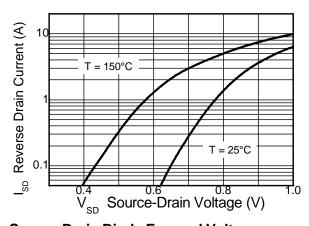




**Typical Transfer Characteristics** 



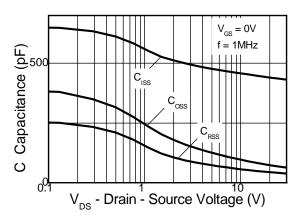




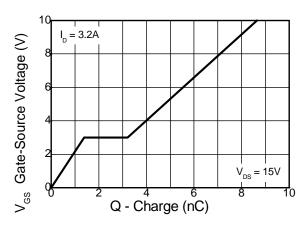
Source-Drain Diode Forward Voltage



## **Typical Characteristics - continued**

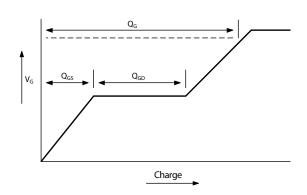


Capacitance v Drain-Source Voltage

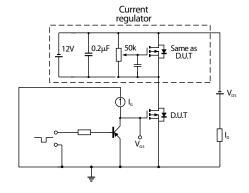


**Gate-Source Voltage v Gate Charge** 

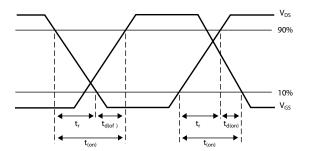
### **Test Circuits**



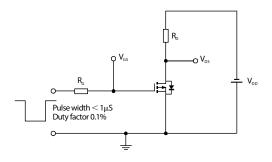
Basic gate charge waveform



Gate charge test circuit



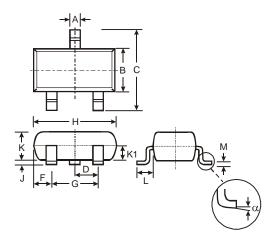
Switching time waveforms



Switching time test circuit

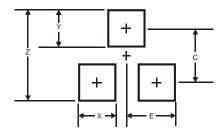


# **Package Outline Dimensions**



SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
J	0.013	0.10	0.05		
K	0.903	1.10	1.00		
K1	-	-	0.400		
L	0.45	0.61	0.55		
M	0.085	0.18	0.11		
α	0°	8°	-		
All Dimensions in mm					

# **Suggested Pad Layout**



Dimensions	Value (in mm)			
Z	2.9			
Х	0.8			
Y	0.9			
С	2.0			
E	1.35			





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